**Features :**

Two anti-paralled thyristors on one Si-wafer
 Hermetic metal cases with ceramic insulators
 Capsule packages for double sided cooling

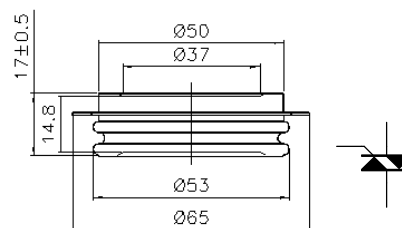
Typical Applications

High power industrial and power transmissior
 DC and AC motor control
 AC controllers

Part No. Y40KSEA-KA37

$I_{T(RMS)}$	830A	
V_{DRM}, V_{RRM}	500V	800V
	1000V	1200V
	1400V	1600V
	1800V	

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_J (°C)	VALUE			UNIT
				Min	Type	Max	
$I_{T(RMS)}$	RMS current	50Hz sine wave Double side cooled,	$T_C=55^\circ\text{C}$ $T_C=85^\circ\text{C}$	125		1210 830	A
V_{DRM}	Repetitive peak reverse voltage	$V_{DRM} \text{ tp}=10\text{ms}$ $V_{DSM}=V_{DRM}+100\text{V}$	125	500		1800	V
I_{DRM}	Repetitive peak current	at V_{DRM}	125			50	mA
I_{TSM}	Surge on-state current	10ms half sine wave	125			7.8	kA
I^2t	I^2t for fusing coordination	$V_R=0.6V_{RRM}$				304	$\text{A}^2\text{s} \times 10^3$
V_{TO}	Threshold voltage		125			1.00	V
r_T	On-state slope resistance		125			0.85	mΩ
V_{TM}	Peak on-state voltage	$I_{TM}=1200\text{A}$, $F=18\text{kN}$	125			2.70	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=0.67V_{DRM}$	125			50	V/μs
di/dt	Critical rate of rise of on-state current	$V_{DM}=67\%V_{DRM}$ to 1000A, Gate pulse $t_r \leq 0.5\mu\text{s}$ $I_{GM}=1.5\text{A}$ Repetitive	125			50	A/μs
I_{GT}	Gate trigger current	$V_A=12\text{V}$, $I_A=1\text{A}$	25	20		350	mA
V_{GT}	Gate trigger voltage			0.8		3.5	V
I_H	Holding current			20		400	mA
I_L	Latching current					500	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	double side cooled Clamping force 18kN				0.030	C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink					0.008	
F_m	Mounting force			15		20	kN
T_{vj}	Junction temperature			-40		125	°C
T_{stg}	Stored temperature			-40		140	°C
W_t	Weight				200		g
Outline	KA37						

Outline:

TECHSEM reserves the right to change specifications without notice.